HUASHUO SEMICONDUCTOR

HSH30P15

P-Ch 150V Fast Switching MOSFETs

Description

The HSH30P15 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

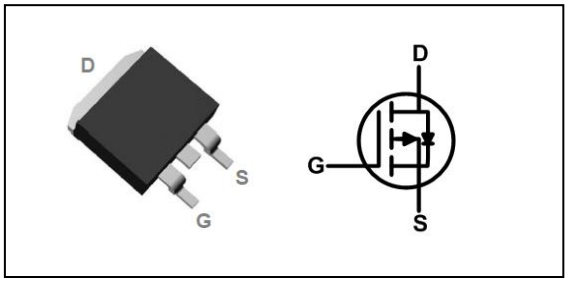
The HSH30P15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-150	V
$R_{DS(ON),typ}$	56	mΩ
I_D	-30	A

TO-263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-30	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ -10V[1]	-20	A
I_{DM}	Pulsed Drain Current[2]	-100	A
EAS	Single Pulse Avalanche Energy[3]	560	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	100	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	1.22	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-150	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-20A	---	56	70	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-2	-3	-4	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-150V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ± 20V , V_{DS}=0V	---	---	± 100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-20A	---	14	---	S
Q_g	Total Gate Charge	V_{DS}=-75V , V_{GS}=-10V , I_D=-20A	---	93	---	nC
Q_{gs}	Gate-Source Charge		---	18	---	
Q_{gd}	Gate-Drain Charge		---	14	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-75V , V_{GS}=-10V , R_G=3.3Ω, I_D=-20A	---	63	---	ns
T_r	Rise Time		---	27	---	
$T_{d(off)}$	Turn-Off Delay Time		---	230	---	
T_f	Fall Time		---	80	---	
C_{iss}	Input Capacitance	V_{DS}=-75V , V_{GS}=0V , f=1MHz	---	5990	---	pF
C_{oss}	Output Capacitance		---	744	---	
C_{rss}	Reverse Transfer Capacitance		---	337	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-30	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.3	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-50V,V_{GS}=-10V,L=0.1mH
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

Figure 1. Output Characteristics

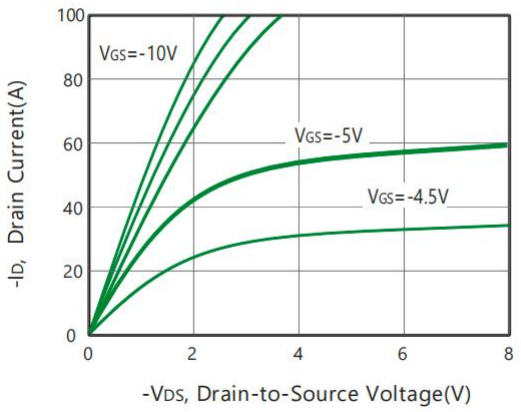


Figure 2. Body Diode Forward Voltage Variation with Source Current

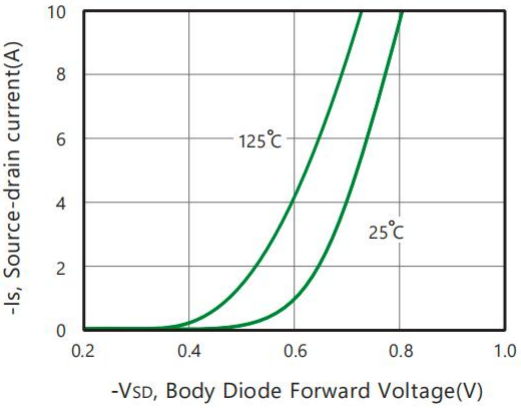


Figure 3. On-Resistance vs. Gate-Source Voltage

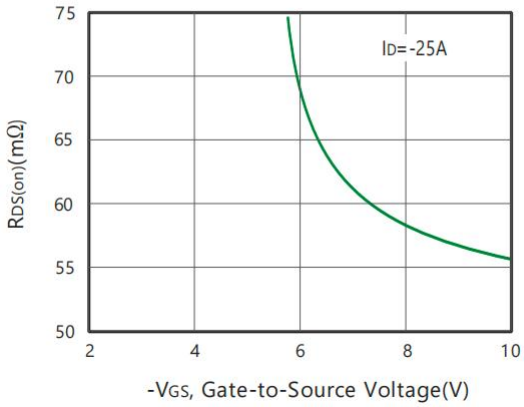


Figure 4. On-Resistance Variation with Drain Current and Temperature

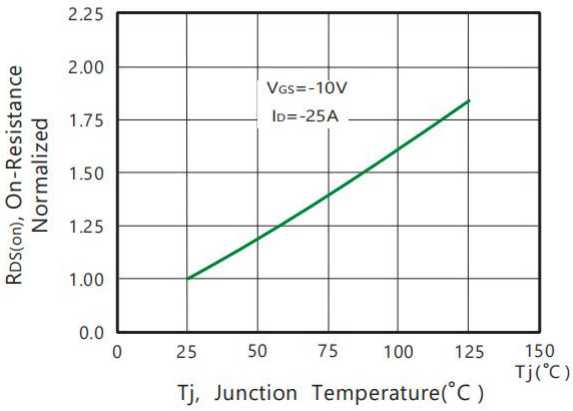


Figure 5. Gate Threshold Variation with Temperature

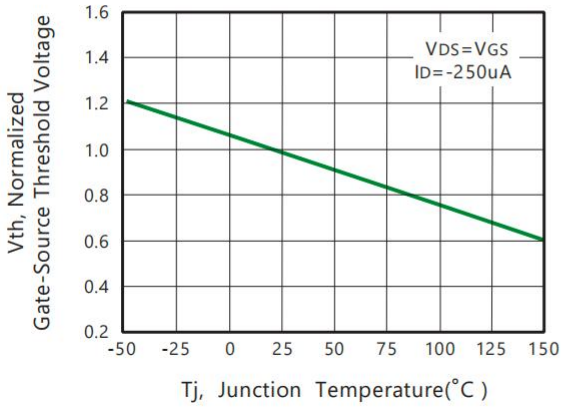


Figure 6. Gate Charge

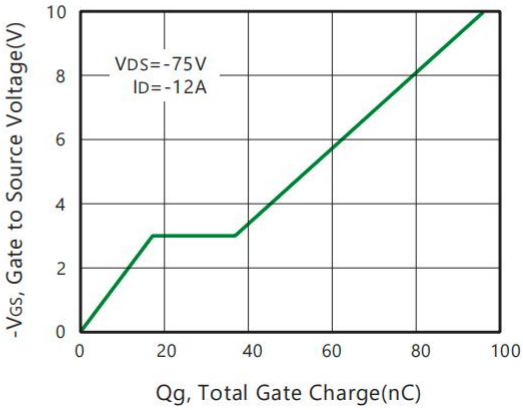


Figure 7. Capacitance

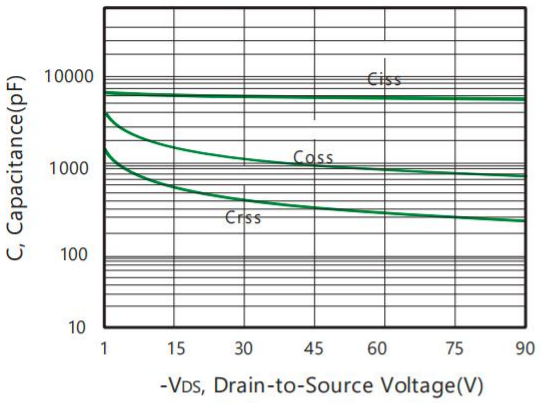
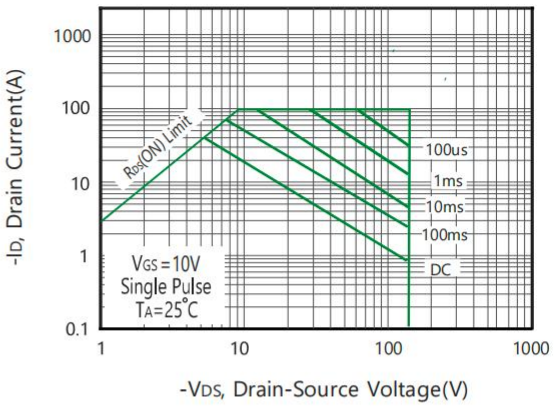


Figure 8. Maximum Safe Operating Area



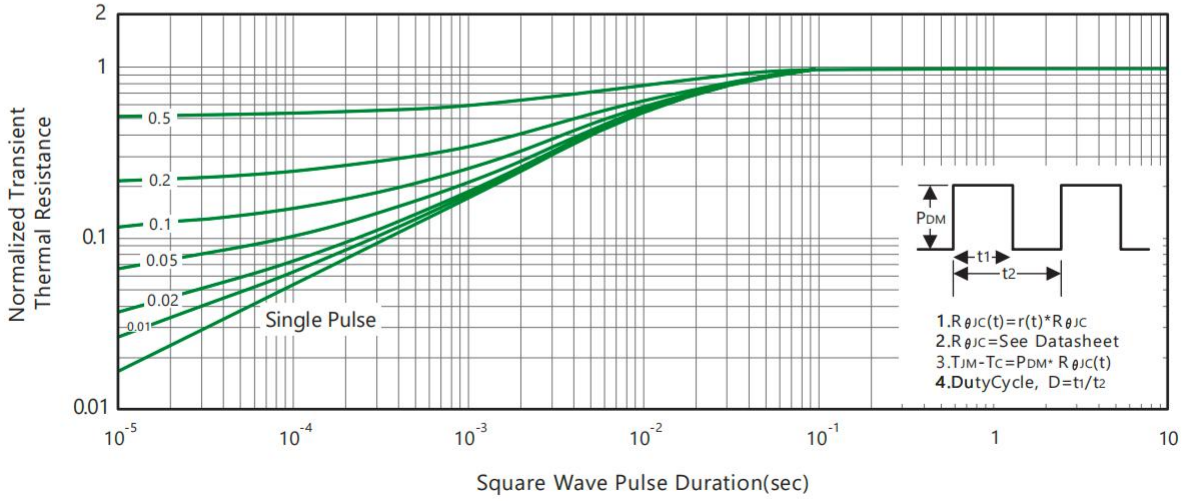
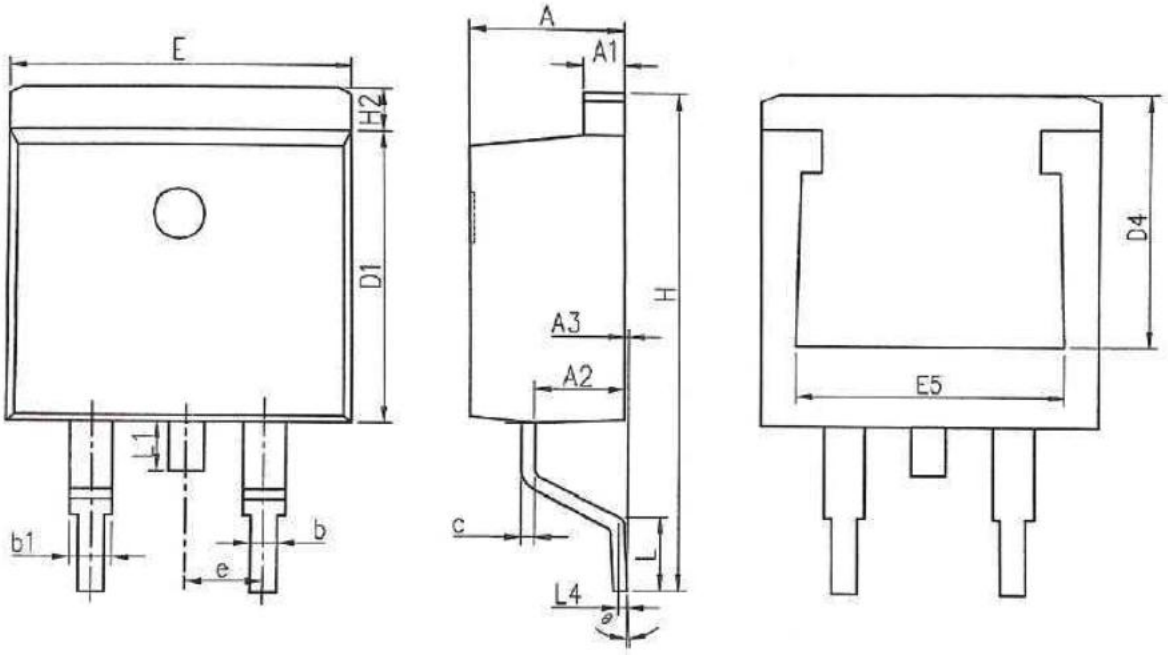


Figure 9. Normalized Thermal Transient Impedance Curve



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.370	4.770	0.172	0.188
A1	1.220	1.420	0.048	0.056
A2	2.200	2.890	0.087	0.114
A3	0.000	0.250	0.000	0.010
b	0.700	0.960	0.028	0.038
b1	1.170	1.470	0.046	0.058
c	0.300	0.530	0.012	0.021
D1	8.500	9.300	0.335	0.366
D4	6.600	-	0.260	-
E	9.860	10.36	0.388	0.408
E5	7.060	-	0.278	-
e	2.540 BSC		0.100 BSC	
H	14.70	15.70	0.579	0.618
H2	1.070	1.470	0.042	0.058
L	2.000	2.600	0.079	0.102
L1	1.400	1.750	0.055	0.069
L4	0.250 BSC		0.010 BSC	
Θ	0°	9°	0°	9°